

1. 41. (Amended) A transistor structure, comprising:

a gate oxide layer over a semiconductive substrate, the gate oxide layer comprising silicon dioxide and having a thickness of about 5Å; the gate oxide layer having a nitrogen-enriched region which is only in an upper half of the gate oxide layer;

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at least one conductive layer over the gate oxide layer; and

source/drain regions within the semiconductive substrate; the source/drain regions being gatedly connected to one another by the conductive layer.

2. 42. The structure of claim 41 wherein the conductive layer comprises conductively-doped silicon.

3. 43. The structure of claim 41 wherein the conductive layer comprises p-type conductively-doped silicon.